



Smart Highside Power Switch

Reversave™

 Reverse battery protection by self turn on of power MOSFET

Features

- Short circuit protection with latch
- Current limitation
- Overload protection
- Thermal shutdown with restart
- Overvoltage protection (including load dump)
- Loss of ground protection
- Loss of V_{bb} protection (with external diode for charged inductive loads)
- Very low standby current
- Fast demagnetization of inductive loads
- Electrostatic discharge (ESD) protection
- Optimized static electromagnetic compatibility (EMC)
- Green Product (RoHS compliant)
- AEC qualified

Product Summary 5.5...62 V Operating voltage $V_{\rm bb(on)}$ On-state resistance RON $20 \text{ m}\Omega$ Nominal current 5.5 Α /L(nom) Load current (ISO) /L(ISO) 17 Α Current limitation 70 Α /L12(SC)

Package

PG-TO252-5-11 (DPAK 5 pin; less than half the size as TO 220 SMD)



Diagnostic Function

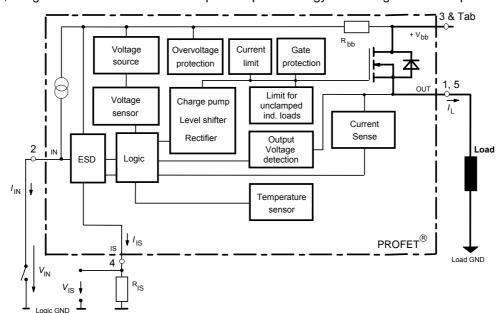
• Proportional load current sense (with defined fault signal in case of overload operation, overtemperature shutdown and/or short circuit shutdown)

Application

- Power switch with current sense diagnostic feedback for 42V and 24 V DC grounded loads
- All types of resistive, inductive and capacitive loads
- Replaces electromechanical relays, fuses and discrete circuits

General Description

N channel vertical power FET with charge pump, current controlled input and diagnostic feedback with load current sense, integrated in Smart SIPMOS® chip on chip technology. Providing embedded protective functions.





Pin	Symbol		Function
1	OUT	0	Output; output to the load; pin 1 and 5 must be externally shorted*.
2	IN	I	Input; activates the power switch if shorted to ground.
Tab/(3)	Vbb	+	Supply Voltage ; positive power supply voltage; tab and pin3 are internally shorted.
4	IS	S	Sense Output ; Diagnostic feedback; provides at normal operation a sense current proportional to the load current; in case of overload, overtemperature and/or short circuit a defined current is provided (see Truth Table on page 8)
5	OUT	0	Output; output to the load; pin 1 and 5 must be externally shorted*.

^{*)} Not shorting all outputs will considerably increase the on-state resistance, reduce the peak current capability and decrease the current sense accuracy

Maximum Ratings at $T_j = 25$ °C unless otherwise specified

Parameter	Symbol	Values	Unit
Supply voltage (overvoltage protection see page 4)	$V_{ m bb}$	62	V
Supply voltage for full short circuit protection 1)	$V_{ m bb}$	48	V
Load dump protection $V_{\text{LoadDump}} = U_{\text{A}} + V_{\text{S}}$, $U_{\text{A}} = 24 \text{ V}$ $R_{\text{I}} = 2 \Omega$, $R_{\text{L}} = 4.4 \Omega$, $t_{\text{d}} = 400 \text{ ms}$, IN= low or high	V _{Load dump} ²⁾	70	V
Load current (Short-circuit current, see page 5)	<i>I</i> _	self-limited	Α
Operating temperature range	$T_{\rm j}$	-40+150	°C
Storage temperature range	$T_{ m stg}$	-55+150	
Power dissipation (DC)	P_{tot}	59	W
Inductive load switch-off energy dissipation, 3)			
single pulse $I_L = 20 \text{ A}$, $V_{bb} = 24 \text{V}$ $T_j = 150 \text{ °C}$:	E _{AS}	0.25	J
Electrostatic discharge capability (ESD) (Human Body Model) acc. ESD assn. std. S5.1-1993; R=1.5kΩ; C=100pF	V _{ESD}	3.0	kV
Current through input pin (DC)	I _{IN}	+15, -120	mA
Current through current sense pin (DC)	I _{IS}	+15, -120	
see internal circuit diagrams page 9			
Input voltage slew rate			
$V_{\rm bb} \le 16 { m V}: \ V_{\rm bb} > 16 { m V}^4:$	dV_{bIN}/dt	self-limited 20	V/μs

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Short circuit is defined as a combination of remaining resistances and inductances. See schematic on page11.

²⁾ V_{Load dump} is setup without the DUT connected to the generator per ISO 7637-1 and DIN 40839

³⁾ See also diagram on page 11.

See also on page 8. Slew rate limitation can be achieved by means of using a series resistor R_{IN} in the input path. This resistor is also required for reverse operation. See also page 10.



Thermal Characteristics

Parameter and Conditions		Symbol	Values			Unit
			min	typ	max	
Thermal resistance	chip - case:	R_{thJC}		-	1.1	K/W
junction - ambient (free air):		R_{thJA}		80		
SMD version	n, device on PCB ⁶⁾ :			45	55	

Electrical Characteristics

Parameter and Conditions	Symbol		Values	}	Unit
at T_j = 25, V_{bb} = 24 V unless otherwise specified		min	typ	max	

Load Switching Capabilities and Characteristics

5 1						
On-state resistance (pin 3 to pin 1,	5)					
V_{IN} = 0, V_{bb} = 5.5V, I_{L} = 7.5 A	<i>T</i> _j =25 °C: <i>T</i> _j =150 °C:	R _{ON}		19 38	25 50	mΩ
V_{IN} = 0, V_{bb} = 1224V, I_{L} = 7.5 A	<i>T</i> _j =25 °C: <i>T</i> _j =150 °C:			16 32	20 40	
Output voltage drop limitation at sn currents (Tab to pin 1,5) 5)	V _{ON(NL)}		40	65	mV	
Nominal load current (Tab to pin 1						
ISO Proposal: $V_{ON} \le 0.5 \text{ V}$, $T_C = 85^{\circ}\text{C}$, $T_i \le 150^{\circ}\text{C}$		$I_{L(ISO)}$	17	21.5		Α
SMD 6), $V_{ON} \le 0.5 \text{ V}$, $T_A = 85^{\circ}\text{C}$, $T_{A} = 85^{\circ}\text{C}$	$T_{\rm j} \leq 150^{\circ}{ m C}$	I _{L(nom)}	5.5	6.5		
Turn-on time	to 90% V _{OUT} :	<i>t</i> on		150	300	μs
Turn-off time	to 10% V _{OUT} :	$t_{ m off}$		200	550	
$R_L = 3.9 \ \Omega, \ T_j = -40150 \ ^{\circ}C$						
Slew rate on		dV/dt _{on}		0.65	1.0	V/µs
25 to 50% V_{OUT} , $R_{\text{L}} = 3.9 \Omega$, $T_{\text{j}} = -40150 ^{\circ}\text{C}$						
Slew rate off 50 to 25% V_{OUT} , $R_{\text{L}} = 3.9 \ \Omega$, $T_{\text{j}} = -40 \ \Omega$	0150 °C	-d V/dt _{off}		0.65	1.2	V/µs

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⁵⁾ See figure 7a on page 15.

⁶⁾ Device on 50mm*50mm*1.5mm epoxy PCB FR4 with 6cm² (one layer, 70μm thick) copper area for V_{bb} connection. PCB is vertical without blown air.



Parameter and Conditions		Symbol	Values			Unit	
at T_j = 25, V_{bb} = 24 V unless otherwise sp	pecified		min.	typ.	max.		
Operating Parameters							
Operating voltage (ViN=0)	<i>T</i> _i =-40150 °C:	$V_{\rm bb(on)}$	5.5		62	V	
Undervoltage shutdown 7) 8)	•	$V_{bIN(u)}$		2.5	3.5	V	
Undervoltage restart of charge pu	ımp	V _{bb(ucp)}		4	5.5	V	
Overvoltage protection 9)		$V_{Z,IN}$	68	73		V	
/ _{bb} =15 mA							
Standby current	<i>T</i> _j =-40+120°C:	I _{bb(off)}		3	6	μΑ	
I _{IN} =0	<i>T</i> _j =150°C:			6	14		
Reverse Battery							
Reverse battery voltage ¹⁰⁾		-V _{bb}			16	V	
On-state resistance (pin 1,5 to pir	า 3)						
$V_{\text{bb}} = -8V$, $V_{\text{IN}} = 0$, $I_{\text{L}} = -7.5$ A, R_{IS}	= 1 k Ω , 8)						
, , _ ,	<i>T</i> _i =25 °C:	R _{ON(rev)}		19	25	mΩ	
	<i>T</i> j=150 °C:			35	44		
V_{bb} = -1224V, V_{IN} = 0, I_{L} = -7.5 A	, $R_{IS} = 1 \text{ k}\Omega$,						
	<i>T</i> j=25 °C:			18	23		
	<i>T</i> _j =150 °C:			33	40		
Integrated resistor in V _{bb} line		R _{bb}		100	150	Ω	
Inverse Operation 11)							
Output voltage drop (pin 1,5 to pin	n 3) ⁸⁾						
$I_L = -7.5 \text{ A}, R_{IS} = 1 \text{ k}\Omega,$	<i>T</i> _i =25 °C:	-V _{ON(inv)}		700		mV	
$I_{L} = -7.5 \text{ A}, R_{IS} = 1 \text{ k}\Omega,$	7j=150 °C:	3 Old(IIIV)		300			
Turn-on delay after inverse opera $V_{IN}(inv) = V_{IN}(fwd) = 0 \text{ V}$	tion; I _L > 0A ⁸⁾	$t_{d(inv)}$		1		ms	

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⁷⁾ VbIN=Vbb-VIN see diagram page 14.

⁸⁾ Not subject to production test, specified by design.

See also $V_{ON(CL)}$ in circuit diagram page 9.

¹⁰⁾ For operation at voltages higher then |16V| please see required schematic on page 10.

Permanent Inverse operation results eventually in a current flow via the intrinsic diode of the power DMOS. In this case the device switches on with a time delay $t_{d(inv)}$ after the transition from inverse to forward mode.



Parameter and Conditions		Symbol	Values		;	Unit
at T_j = 25, V_{bb} = 24 V unless otherwise speci	fied		min.	typ.	max.	
Protection Functions 12)				<u> </u>		
Short circuit current limit (Tab to pin	1,5) ¹³⁾					
Short circuit current limit at $V_{ON} = 6V^{14}$	T _j =-40°C: T _j =25°C: T _j =+150°C:	I _{L6(SC)}	 50	90 80 65	110 	А
Short circuit current limit at $V_{ON} = 12V^{-14}$	T _j =-40°C: T _j =25°C: T _j =+150°C:	/L12(SC)	 40	80 70 55	100 	А
Short circuit current limit at $V_{ON} = 18V^{-14}$	T _j =-40°C: T _j =-25°C: T _j =+150°C:	I _{L18(SC)}	 30	55 50 48	80 	A
Short circuit current limit at $V_{ON} = 24V$ $t_{m}=170 \mu s$	T _j =-40°C: T _j =25°C: T _j =+150°C:	<i>I</i> L24(SC)	 25	45 40 35	60 	Α
Short circuit current limit at $V_{ON} = 30V$ $t_{m} = 170 \mu s$	T _j =-40°C: T _j =25°C: T _j =+150°C:	<i>I</i> L30(SC)	 20	30 30 30	50 	Α
Short circuit current limit at $V_{ON} = 45 \text{V}^{-14}$	T _j =-40°C: T _j =25°C: T _j =+150°C:	<i>I</i> L45(SC)	 15	22 22 22	35 	Α
Short circuit shutdown detection volta (pin 3 to pins 1,5)	age	V _{ON(SC)}	2.5	3.5	4.5	V
Short circuit shutdown delay after input current positive slope, $V_{\rm ON} > V_{\rm ON(SC)}$, $T_{\rm j} = -40+150$ °C min. value valid only if input "off-signal" time exceeds 30 μ s		t _{d(SC1)}	350	650	1200	μs
Short circuit shutdown delay during of $V_{\text{ON}} > V_{\text{ON(SC)}}$	on condition ¹³⁾	$t_{d(SC2)}$		2		μs
Output clamp (inductive load switch off) ¹⁵⁾ at $V_{OUT} = V_{bb} - V_{ON(CL)}$ (e.g. overvoltage) $I_{L} = 40 \text{ mA}$		V _{ON(CL)}	63	67		V
Thermal overload trip temperature		T_{jt}	150	175		°C
Thermal hysteresis		$\Delta T_{\rm jt}$		10		K

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¹²⁾ Integrated protection functions are designed to prevent IC destruction under fault conditions described in the data sheet. Fault conditions are considered as "outside" normal operating range. Protection functions are not designed for continuous repetitive operation.

¹³⁾ Short circuit current limit for max. duration of $t_{d(SC1)}$, prior to shutdown, see also figures 3.x on page 13.

¹⁴⁾ Not subject to production test, specified by design.

¹⁵⁾ See also figure 2b on page 12.



Parameter and Conditions	Symbol		Values	•	Unit
at T_j = 25, V_{bb} = 24 V unless otherwise specified		min.	typ.	max.	
Diagnostic Characteristics					
Current sense ratio, static on-condition $k_{\rm ILIS} = I_{\rm L}: I_{\rm IS}, I_{\rm IS} < I_{\rm IS, lim}$ ¹⁶⁾ , $V_{\rm IS} < V_{\rm OUT}$ - 5 V, $V_{\rm bIN} > 4.5$ V	k _{ILIS}		9000		
IL = 30A, Tj = -40°C: Tj = +25°C: Tj = +150°C:		8300 8200 8100	9000 9000 8800	10000 9800 9500	
IL = 7.5A, Tj = -40°C: Tj = +25°C: Tj = +150°C:		8200 8100 8000	8900 8900 8700	10000 9800 9500	
IL = 2.5A, Tj = -40°C: Tj = +25°C: Tj = +150°C:		7200 7500 7700	8900 8900 8700	11000 10600 10000	
IL = 0.5A, Tj = -40°C: Tj = +25°C: Tj = +150°C:		5000 6000 7500	9500 10000 10500	16000 15000 13000	
$I_{IN} = 0$ (e.g. during deenergizing of inductive loads):			0		
Sense current under fault conditions $^{17)}$ V_{ON} >1V, typ T_j = -40+150°C:	I _{IS,fault}	4.0	5.2	7.5	mA
Sense current saturation V_{ON} <1V, typ $T_j = -40+150$ °C:	I _{IS,lim}	4.0	6.0	7.5	mA
Fault-Sense signal delay after input current positive slope, $V_{ON} > 1V$, $T_j = -40+150$ °C	t _{delay(fault)}	350	650	1200	μs
Current sense leakage current, I _{IN} = 0	I _{IS(LL)}		0.1	0.5	μΑ
Current sense offset current, $V_{IN} = 0$, $I_L \le 0$	I _{IS(LH)}		1.0	2.0	μΑ
Current sense settling time to $I_{\text{IS static}}$ after input current positive slope, ¹⁸⁾ $I_{\text{L}} = 0 $	$t_{ m son(IS)}$		250	500	μs
Current sense settling time during on condition, ¹⁸⁾ $I_{L} = 10 - 20 \text{ A}, T_{j} = -40+150 ^{\circ}\text{C}$	$t_{ m slc(IS)}$		50	100	μs
Overvoltage protection $I_{bb} = 15 \text{mA}$ $T_j = -40+150^{\circ}\text{C}$:	$V_{z,IS}$	68	73		V

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¹⁶⁾ See also figures 4.x and 6.x on page 13 and 14.

Fault conditions are overload during on (i.e. $V_{ON}>1V$ typ.), overtemperature and short circuit; see also truth table on page 8.

¹⁸⁾ Not subject to production test, specified by design.



PROFET® BTS 6163 D

Parameter and Conditions	Symbol	Values			Unit
at T_j = 25, V_{bb} = 24 V unless otherwise specified		min.	typ.	max.	
Input					
Required current capability of input switch $T_j = -40+150$ °C:	I _{IN(on)}		1.6	2.4	mA
Input current for turn-off $T_j = -40+150$ °C:	I _{IN(off)}			30	μA

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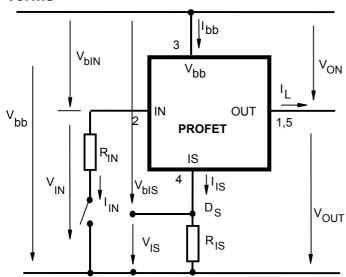


Truth Table

	Input Current	Output	Current Sense
	level	level	lis
Normal	L	L	≈0 (/ _{IS(LL)})
operation	Н	Н	nominal
Overload ¹⁹⁾	L	L	≈ 0 (/ IS(LL))
	Н	Н	I _{IS,fault}
Short circuit to GND ²⁰⁾	L	L	≈ 0 (/ IS(LL))
	н	L	I _{IS,fault}
Overtemperature	L	L	≈ 0 (/ IS(LL))
	Н	L	I _{IS,fault}
Short circuit to Vbb	L	Н	≈ 0 (/ IS(LL))
	Н	Н	<nominal <sup="">21)</nominal>
Open load	L	Z	≈ 0 (/ IS(LL))
	Н	Н	≈0 (/ _{IS(LH)})

L = "Low" Level, H = "High" Level Z = high impedance, potential depends on external circuit

Terms



Two or more devices can easily be connected in parallel to increase load current capability.

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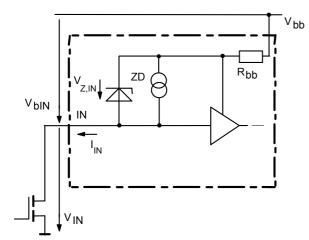
¹⁹⁾ Overload is detected at the following condition: 1V (typ.) < $V_{\rm ON}$ < 3.5V (typ.). See also page 11.

Short Circuit is detected at the following condition: $V_{oN} > 3.5 \text{V}$ (typ.). See also page 11.

Low ohmic short to V_{bb} may reduce the output current I_{L} and therefore also the sense current I_{IS} .



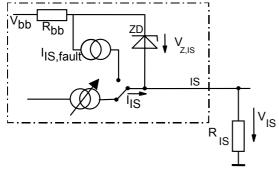
Input circuit (ESD protection)



ESD-Zener diode: 73 V typ.., max 15 mA;

Current sense output

Normal operation

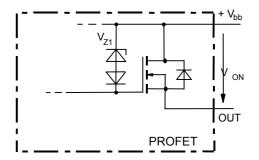


 $V_{\rm Z,IS}$ = 73 V (typ.), $R_{\rm IS}$ = 1 k Ω nominal (or 1 k Ω /n, if n devices are connected in parallel). $I_{\rm S}$ = $I_{\rm L}/k_{\rm ilis}$ can be only driven by the internal circuit as long as $V_{\rm out}$ - $V_{\rm IS}$ > 5V. Therefore R_{IS} should be less than

$$\frac{V_{bb} - 5V}{7.5mA}$$

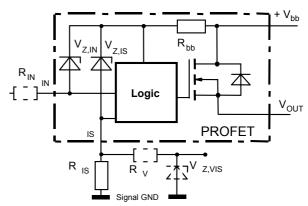
Note: For large values of R_{IS} the voltage V_{IS} can reach almost V_{bb} . See also overvoltage protection. If you don't use the current sense output in your application, you can leave it open.

Inductive and overvoltage output clamp



 V_{ON} is clamped to $V_{ON(Cl)} = 67 \text{ V typ}$

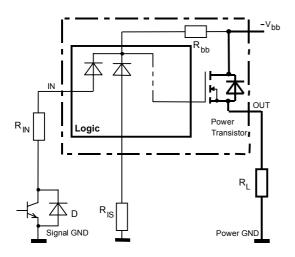
Overvoltage protection of logic part



 R_{bb} = 100 Ω typ., $V_{Z,IN}$ = $V_{Z,IS}$ = 73 V typ., R_{IS} = 1 k Ω nominal. Note that when overvoltage exceeds 73 V typ. a voltage above 5V can occur between IS and GND, if $R_{V},\,V_{Z,VIS}$ are not used.



Reversave™ (Reverse battery protection)



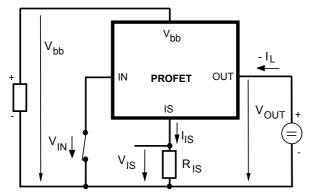
 R_{IS} typ. 1 k Ω . Add R_{IN} for reverse battery protection in applications with V_{bb} above 16V;

recommended value:
$$\frac{1}{R_{\mathit{IN}}} + \frac{1}{R_{\mathit{IS}}} = \frac{0.08A}{\mid V_{\mathit{bb}} \mid -12V}$$

To minimise power dissipation at reverse battery operation, the overall current into the IN and IS pin should be about 80mA. The current can be provided by using a small signal diode D in parallel to the input switch, by using a MOSFET input switch or by proper adjusting the current through $R_{\rm IS}$.

Since the current via $R_{\rm bb}$ generates additional heat in the device, this has to be taken into account in the overall thermal consideration.

Inverse load current operation



The device can be operated in inverse load current mode ($V_{\rm OUT} > V_{\rm bb} > 0$ V). The current sense feature is not available during this kind of operation ($I_{\rm IS} = 0$). In case of inverse operation the intrinsic drain source diode is eventually conducting resulting in considerably increased power dissipation.

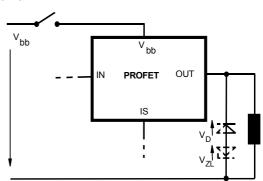
The transition from inverse to forward mode can result in a delayed switch on.

Note: Temperature protection during inverse load current operation is not possible!

V_{bb} disconnect with energised inductive load

Provide a current path with load current capability by using a diode, a Z-diode, or a varistor. ($V_{ZL}+V_D$ <63 V if $R_{IN}=0$). For higher clamp voltages currents at IN and IS have to be limited to 120 mA.

Version a:



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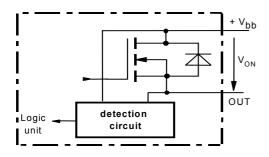


Short circuit detection

Fault Condition: $V_{ON} > V_{ON(SC)}$ (3.5 V typ.) and t> $t_{d(SC)}$ (typ.650 µs).

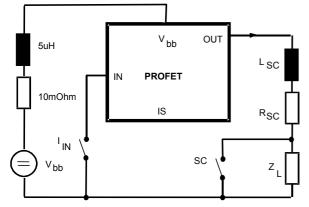
Overload detection

Fault Condition: $V_{ON} > 1 \text{ V typ.}$

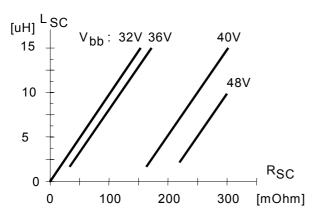


Short circuit

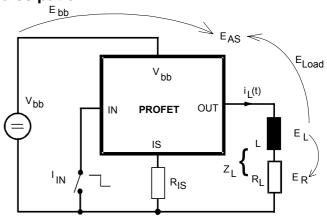
Short circuit is a combination of primary and secondary impedance's and a resistance's.



Allowable combinations of minimum, secondary resistance for full protection at given secondary inductance and supply voltage for single short circuit event:



Inductive load switch-off energy dissipation



Energy stored in load inductance:

$$E_{\rm L} = \frac{1}{2} \cdot {\rm L} \cdot {\rm I}_{\rm L}^2$$

While demagnetizing load inductance, the energy dissipated in PROFET is

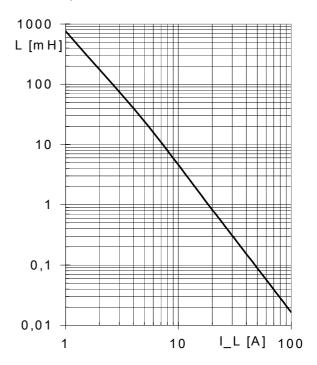
$$E_{AS} = E_{bb} + E_L - E_R = \int V_{ON(CL)} \cdot i_L(t) dt$$

with an approximate solution for $R_L > 0\Omega$:

$$E_{AS} = \frac{I_L \cdot L}{2 \cdot R_L} (V_{bb} + |V_{OUT(CL)}|) ln (1 + \frac{I_L \cdot R_L}{|V_{OUT(CL)}|})$$

Maximum allowable load inductance for a single switch off

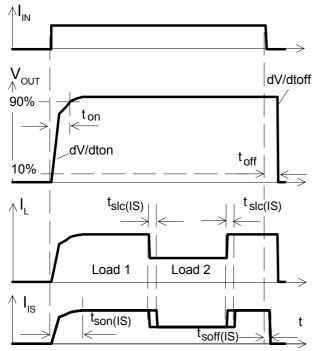
$$L = f(I_L)$$
; T_{j,start} = 150°C, V_{bb} = 24 V, R_L = 0 Ω





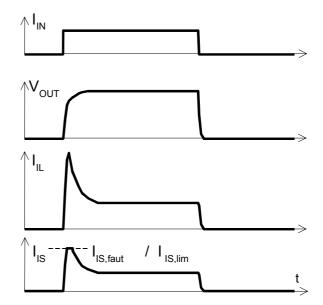
Timing diagrams

Figure 1a: Switching a resistive load, change of load current in on-condition:



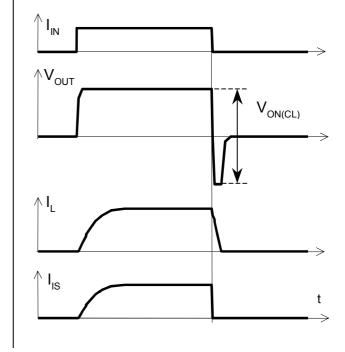
The sense signal is not valid during a settling time after turn-on/off and after change of load current.

Figure 2a: Switching motors and lamps:



As long as $V_{blS} < V_{Z,lS}$ the sense current will never exceed $I_{lS,fault}$ and/or $I_{lS,lim}$.

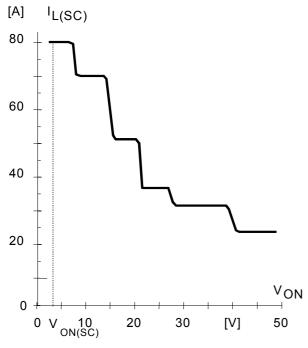
Figure 2b: Switching an inductive load:



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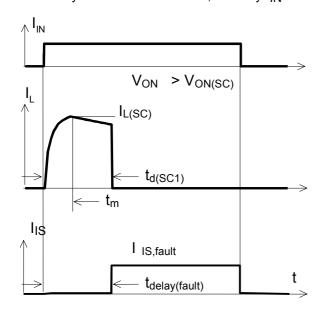


Figure 3a: Typ. current limitation characteristic



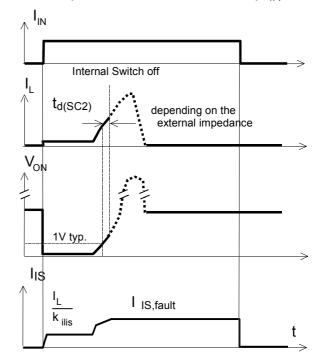
In case of $V_{ON} > V_{ON(SC)}$ (typ. 3.5 V) the device will be switched off by internal short circuit detection.

Figure 3b: Short circuit type one: shut down by short circuit detection, reset by $I_{IN} = 0$.



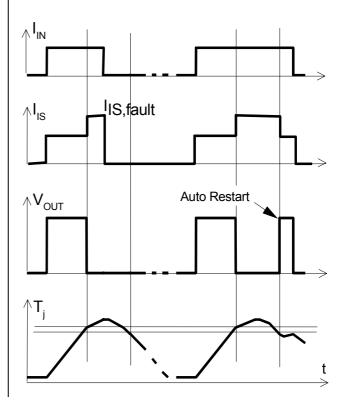
Shut down remains latched until next reset via input.

Figure 3c: Short circuit type two: shut down by short circuit detection, reset by $I_{IN} = 0$.



Shut down remains latched until next reset via input.

Figure 4a: Overtemperature Reset if $T_i < T_{it}$



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Figure 4b: Overload

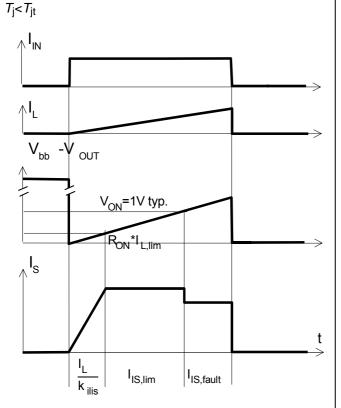


Figure 5a: Undervoltage restart of charge pump, overvoltage clamp

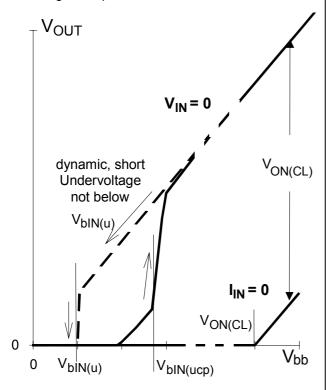


Figure 6a: Current sense versus load current:

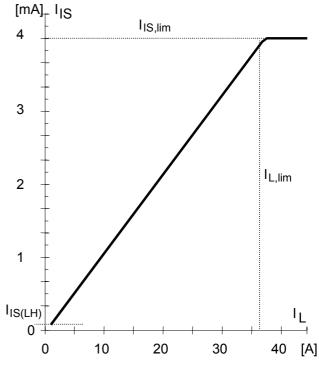
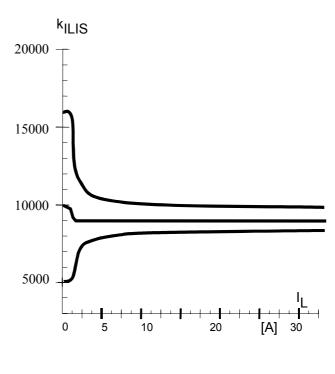


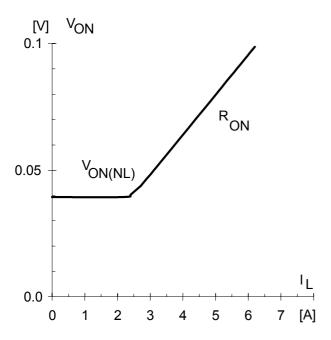
Figure 6b: Current sense ratio²²:



This range for the current sense ratio refers to all devices. The accuracy of the k_{ILIS} can be raised by means of calibration the value of k_{ILIS} for every single device.



Figure 7a: Output voltage drop versus load current:



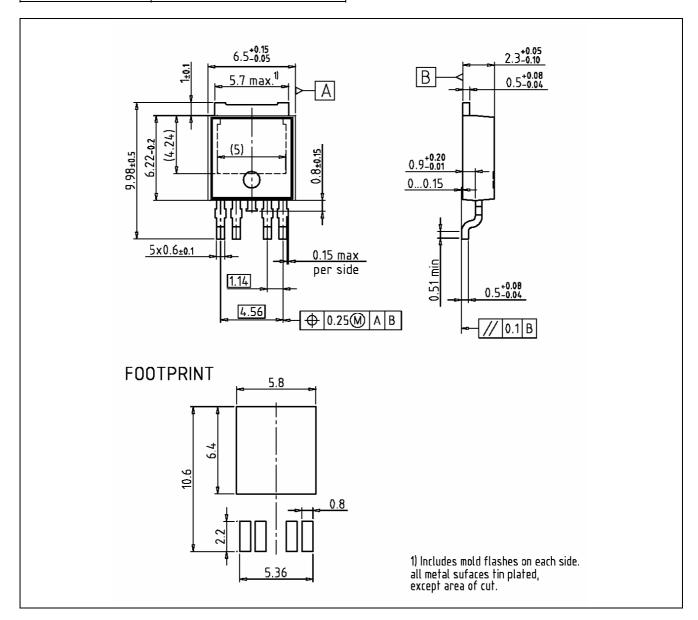


Package Outlines

All dimensions in mm

D-Pak-5 Pin: PG-TO252-5-11

Sales Code BTS6163D



Green Product (RoHS compliant)

To meet the world-wide customer requirements for environmentally friendly products and to be compliant with government regulations the device is available as a green product. Green products are RoHS-Compliant (i.e Pbfree finish on leads and suitable for Pb-free soldering according to IPC/JEDEC J-STD-020).

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Revision History

Version	Date	Changes
Rev. 1.0	2007-02-21	RoHS-compliant version of BTS6163D
		Page 1, page 16: RoHS compliance statement and Green product feature added
		Page 1, page 16: Change to RoHS compliant package PG-TO252-5-11
		Legal disclaimer updated

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